

XN01112 (XN1112)

Silicon PNP epitaxial planar type

For switching/digital circuits

■ Features

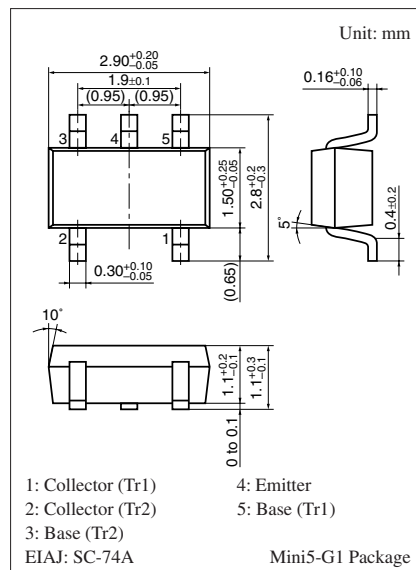
- Two elements incorporated into one package
(Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- UNR2112 (UN2112) × 2

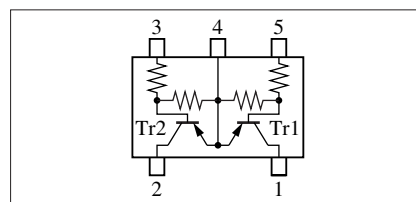
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Collector current	I_C	-100	mA
Total power dissipation	P_T	300	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 7K

Internal Connection



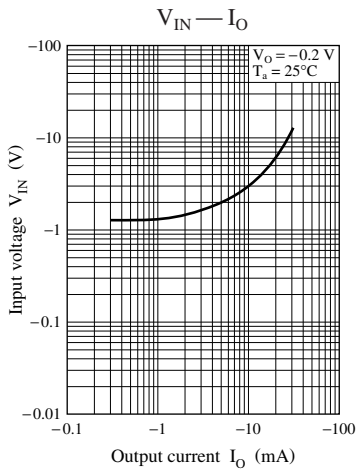
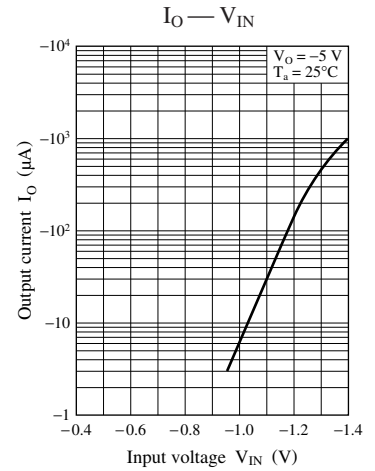
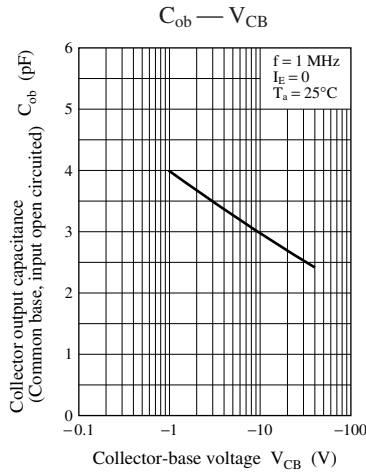
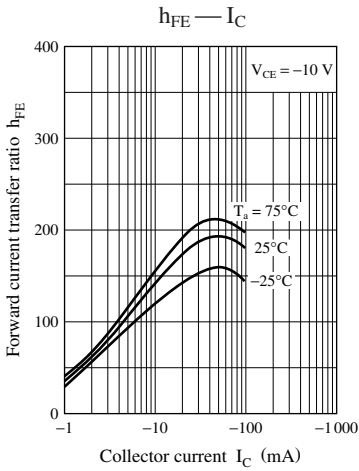
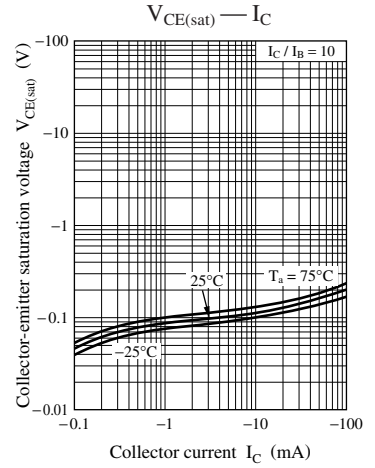
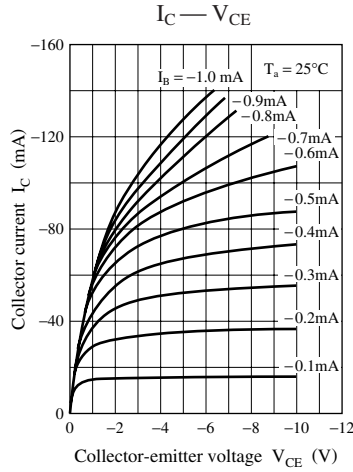
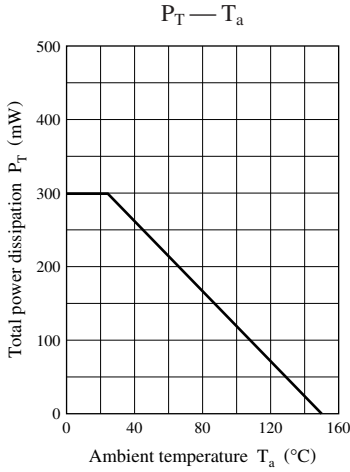
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{V}, I_B = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{V}, I_C = 0$			-0.2	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{V}, I_C = -5 \text{mA}$	60			—
h_{FE} Ratio *	$h_{FE(\text{Small})} / h_{FE(\text{Large})}$	$V_{CE} = -10 \text{V}, I_C = -5 \text{mA}$	0.50	0.99		—
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -10 \text{mA}, I_B = -0.3 \text{mA}$			-0.25	V
Output voltage high-level	V_{OH}	$V_{CC} = -5 \text{V}, V_B = -0.5 \text{V}, R_L = 1 \text{k}\Omega$	-4.9			V
Output voltage low-level	V_{OL}	$V_{CC} = -5 \text{V}, V_B = -2.5 \text{V}, R_L = 1 \text{k}\Omega$			-0.2	V
Input resistance	R_1		-30%	22	+30%	$\text{k}\Omega$
Resistance ratio	R_1 / R_2		0.8	1.0	1.2	—
Transition frequency	f_T	$V_{CB} = -10 \text{V}, I_E = 1 \text{mA}, f = 200 \text{MHz}$		80		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.



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